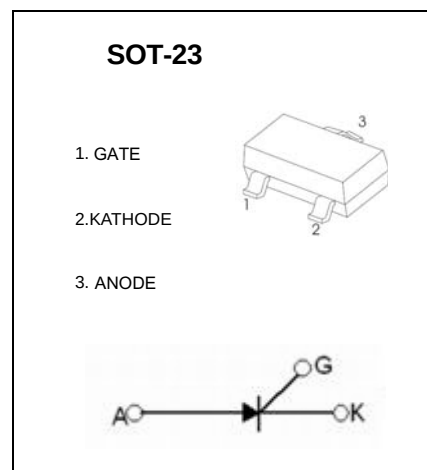


Plastic-Encapsulate Thyristors

Silicon Controlled Rectifier

FEATURES

- Current- I_{GT} : 200 μA
- I_{TRMS} : 0.8 A
- V_{RRM}/V_{DRM} : MCRN100-6: 400 V
MCRN100-8: 600 V
- Operating and storage junction temperature range
 T_J, T_{stg} : -55°C to +150°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol		Test conditions	Min	Max	Unit
On state voltage	V_{TM}^*		$I_{TM}=1A$		1.7	V
Gate trigger voltage	V_{GT}		$V_{AK}=7V$		0.8	V
Peak Repetitive forward and reverse blocking voltage MCRN100-6 MCRN100-8	V_{DRM} AND V_{RRM}		$I_{DRM}=10\mu A$	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}		$V_{AK}=\text{Rated}$ V_{DRM} or V_{RRM}		10	μA
Holding current	I_H		$I_{HL}=20mA, V_{AK}=7V$		5	mA
Gate trigger current	I_{GT}	A2	$V_{AK}=7V$	5	15	μA
		A1		15	30	μA
		A		30	80	μA
		B		80	200	μA

* Forward current applied for 1 ms maximum duration, duty cycle $\leq 1\%$.



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MCRN100-6-8

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Typical Characteristics

